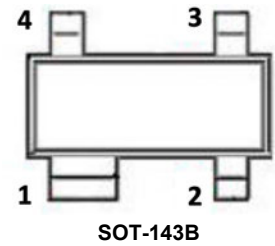


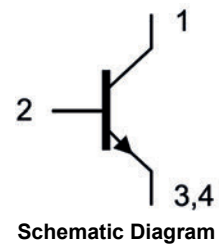
**Features**

- Collector-emitter breakdown voltage:  $V_{(BR)CEO}=10V$  (Min.)
- Minimum lot-to-lot variations for robust device performance and reliable operation



**Applications**

- Designed for low high speed amplifier applications



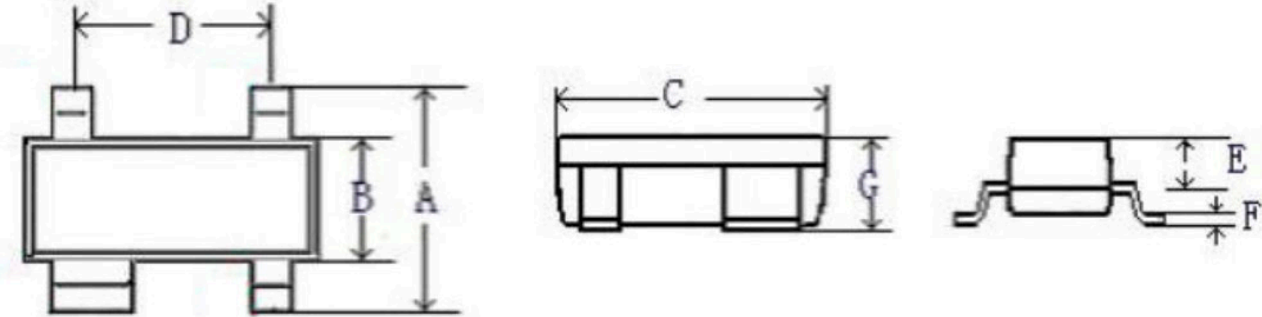
**Absolute Maximum Ratings** ( $T_A=25^{\circ}C$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	10	V
Emitter-Base Voltage	$V_{EBO}$	2.5	V
Collector Current-Continuous	$I_C$	0.12	A
Collector Current-Peak	$I_{CM}$	0.48	A
Collector Power Dissipation @ $T_C=25^{\circ}C$	$P_C$	0.2	W
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	-65 To +150	$^{\circ}C$

**Electrical Characteristics** ( $T_C=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1\mu A, I_E=0$	20	-	-	V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=10V, I_E=0$	-	-	0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=1V, I_C=0$	-	-	0.1	$\mu A$
DC Current Gain	$h_{FE}$	$I_C=15mA, V_{CE}=5V$	90	150	250	-
Output Capacitance	$C_{OB}$	$V_{CB}=8V, I_E=0mA, F=1MHz$	-	0.65	-	pF
Current-Gain - Bandwidth Product	$f_T$	$V_{CE}=8V, I_C=40mA, F=1GHz$	-	9	-	GHz

**Package Outline Dimensions (SOT-143B)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.50	0.094	0.098
B	1.20	1.40	0.047	0.055
C	2.80	3.00	0.110	0.118
D	1.90 TYP		0.075 TYP	
F	0.45	0.55	0.018	0.022
G	0.09	0.15	0.004	0.006
H	1.70 TYP		0.067 TYP	